

# SANYO Semiconductors

# DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

# **2SK4087LS** — General-Purpose Switching Device Applications

#### **Features**

- ON-resistance RDS(on)= $0.47\Omega$  (typ.)
- · 10V drive

• Input capacitance Ciss=1200pF (typ.)

#### **Specifications**

Absolute Maximum Ratings at Ta=25°C

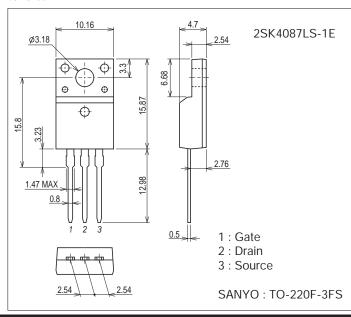
| Parameter                          | Symbol             | Conditions   | Ratings     | Unit |
|------------------------------------|--------------------|--|-------------|------|
| Drain-to-Source Voltage            | V <sub>DSS</sub>   |  | 600         | V    |
| Gate-to-Source Voltage             | V <sub>GSS</sub>   |  | ±30         | V    |
| D. (1.0)                           | I <sub>Dc</sub> *1 | Limited only by maximum temperature Tch=150°C        | 14          | Α    |
| Drain Current (DC)                 |                    | Tc=25°C (SANYO's ideal heat dissipation condition)*3 | 9.2         | Α    |
| Drain Current (Pulse)              | IDP                | PW≤10μs, duty cycle≤1%                               | 52          | А    |
| Allemakia Damas Disainakias        | Do                 |  | 2.0         | W    |
| Allowable Power Dissipation        | PD                 | Tc=25°C (SANYO's ideal heat dissipation condition)*3 | 40          | W    |
| Channel Temperature                | Tch                |  | 150         | °C   |
| Storage Temperature                | Tstg               |  | -55 to +150 | °C   |
| Avalanche Energy (Single Pulse) *4 | EAS                |  | 106         | mJ   |
| Avalanche Current *5               | IAV                |  | 14          | Α    |

<sup>\*1</sup> Shows chip capability.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

#### **Package Dimensions**

unit : mm (typ) 7528-001



#### **Product & Package Information**

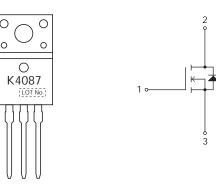
Package : TO-220F-3FSJEITA, JEDEC : SC-67

JEHA, JEDEC . SC-07

• Minimum Packing Quantity : 50 pcs./magazine

#### Marking

## **Electrical Connection**



#### **SANYO Semiconductor Co., Ltd.**

http://www.sanyosemi.com/en/network/

<sup>\*2</sup> Package limited.

<sup>\*3</sup> SANYO's condition is radiation from backside.

<sup>\*4</sup> VDD=50V, L=1mH, IAV=14A (Fig.1)

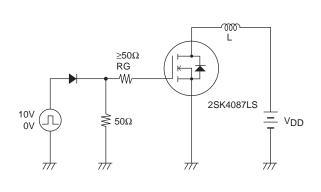
<sup>\*5</sup> L≤1mH, Single pulse

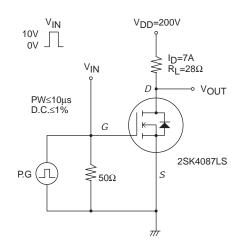
#### Electrical Characteristics at Ta=25°C

| Parameter                                  | Symbol                | bol Conditions                             |     | Ratings |      |      |  |
|--|-----------------------|--|-----|---------|------|------|--|
| Parameter                                  | Symbol                | Conditions                                 | min | typ     | max  | Unit |  |
| Drain-to-Source Breakdown Voltage          | V(BR)DSS              | ID=10mA, VGS=0V                            | 600 |         |      | V    |  |
| Zero-Gate Voltage Drain Current            | IDSS                  | V <sub>DS</sub> =480V, V <sub>GS</sub> =0V |     |         | 100  | μΑ   |  |
| Gate-to-Source Leakage Current             | IGSS                  | V <sub>GS</sub> =±30V, V <sub>DS</sub> =0V |     |         | ±100 | nA   |  |
| Cutoff Voltage                             | V <sub>GS</sub> (off) | V <sub>DS</sub> =10V, I <sub>D</sub> =1mA  | 3   |         | 5    | V    |  |
| Forward Transfer Admittance                | yfs                   | V <sub>DS</sub> =10V, I <sub>D</sub> =7A   | 4   | 8       |      | S    |  |
| Static Drain-to-Source On-State Resistance | R <sub>DS</sub> (on)  | I <sub>D</sub> =7A, V <sub>GS</sub> =10V   |     | 0.47    | 0.61 | Ω    |  |
| Input Capacitance                          | Ciss                  |  |     | 1200    |      | pF   |  |
| Output Capacitance                         | Coss                  | V <sub>DS</sub> =30V, f=1MHz               |     | 220     |      | pF   |  |
| Reverse Transfer Capacitance               | Crss                  |  |     | 50      |      | рF   |  |
| Turn-ON Delay Time                         | t <sub>d</sub> (on)   |  |     | 27      |      | ns   |  |
| Rise Time                                  | t <sub>r</sub>        | San Fig 2                                  |     | 72      |      | ns   |  |
| Turn-OFF Delay Time                        | t <sub>d</sub> (off)  | See Fig.2                                  |     | 144     |      | ns   |  |
| Fall Time                                  | t <sub>f</sub>        |  |     | 48      |      | ns   |  |
| Total Gate Charge                          | Qg                    |  |     | 46      |      | nC   |  |
| Gate-to-Source Charge                      | Qgs                   | $V_{DS}=200V$ , $V_{GS}=10V$ , $I_{D}=14A$ |     | 8.6     |      | nC   |  |
| Gate-to-Drain "Miller" Charge              | Qgd                   |  |     | 26.4    |      | nC   |  |
| Diode Forward Voltage                      | V <sub>SD</sub>       | I <sub>S</sub> =14A, V <sub>GS</sub> =0V   |     | 0.95    | 1.3  | V    |  |

Fig.1 Unclamped Inductive Switching Test Circuit

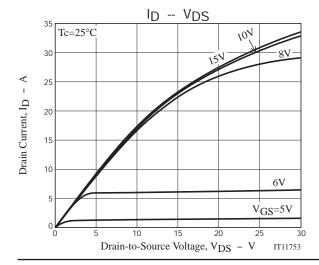
Fig.2 Switching Time Test Circuit

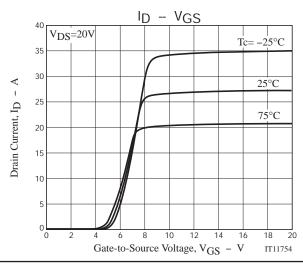


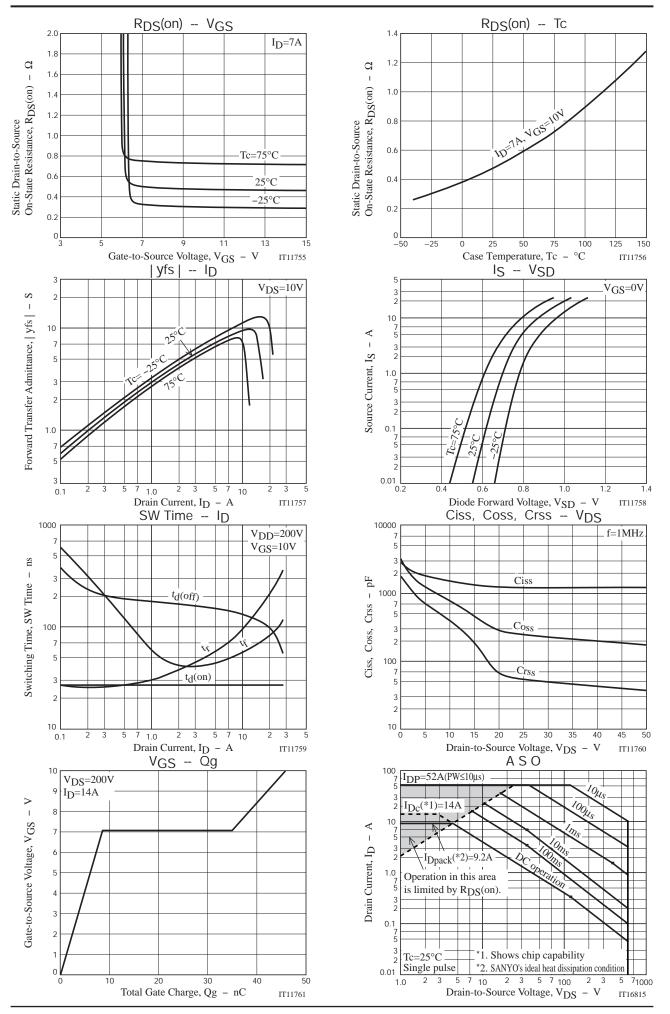


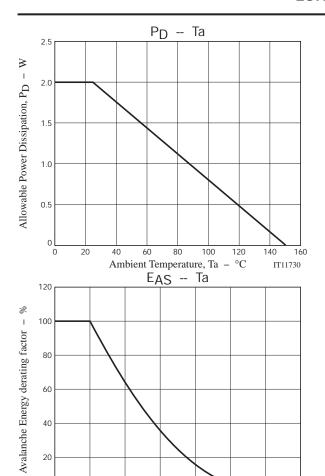
#### **Ordering Information**

| Device       | Package     | Shipping        | memo    |
|--------------|-------------|-----------------|---------|
| 2SK4087LS-1E | TO-220F-3FS | 50pcs./magazine | Pb Free |









75

Ambient Temperature, Ta - °C

100

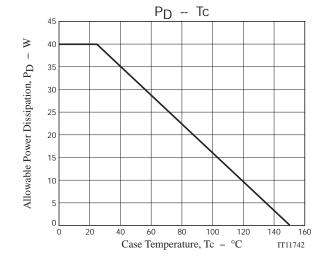
125

175

IT10478

150

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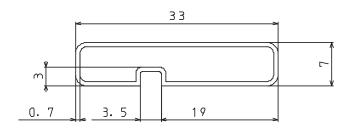
#### Magazine Specification

2SK4087LS-1E

#### 1. Packing Format

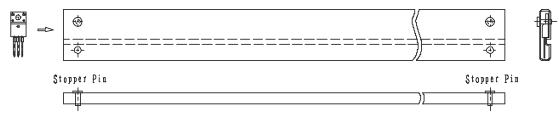
| Package Name          | Magazine Name    |    | Maximum Number of<br>devices contained (pcs) |           | Packing format  |  |  |
|-----------------------|------------------|----|--|-----------|---|--|--|
| 1 4 4 4 4 4 1 4 4 4 4 | Ida 9 and 14 and | l  | Inner box                                    | Outer box | Inner BOX   | Outer BOX  |  |
| TO-220F-3F\$          | TO-220F          | 50 | 1, 000                                       | 4,000     | SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55 | SPT-081029<br>4 inner boxes contained<br>Dimensions:mm (external)<br>590×225×178 |  |

## 



Tolerance=±0, 3mm
Thickness=0, 7±0, 2mm
Length =532, 5±2mm
Material =PVC (Antistatic treatment)

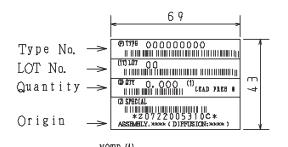
### 3. Storage method to magazine

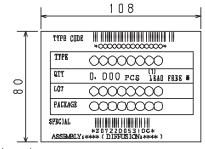


4. Inner box label (unit:mm)



It is a label at the time of factory shigments. The form of a label may change in physical distribution process.



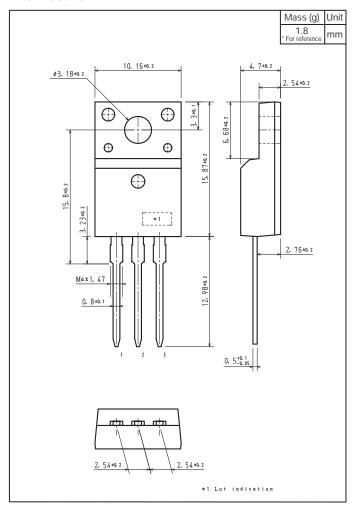


The LEAD FREE \* description shows that the surface treatment of the terminal is lead free.

| Label       | JEITA Phase    |  |  |  |
|-------------|----------------|--|--|--|
| LEAD FREE 3 | JEITA Phase 3A |  |  |  |

# **Outline Drawing**

2SK4087LS-1E



Note on usage: Since the 2SK4087LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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